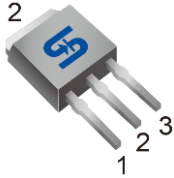


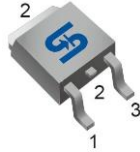
# TSM900N06

## 60V N-Channel Power MOSFET

**TO-251S  
(IPAK SL)**



**TO-252  
(DPAK)**



**Pin Definition:**

1. Gate
2. Drain
3. Source

### Key Parameter Performance

| Parameter          | Value           | Unit |
|--------------------|-----------------|------|
| $V_{DS}$           | 60              | V    |
| $R_{DS(on)}$ (max) | $V_{GS} = 10V$  | 90   |
|                    | $V_{GS} = 4.5V$ | 100  |
| $Q_g$              | 9.3             | nC   |

**SOT-223**

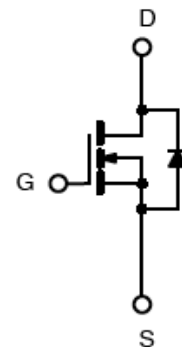


### Ordering Information

| Part No.        | Package | Packing            |
|-----------------|---------|--------------------|
| TSM900N06CH X0G | TO-251S | 75pcs / Tube       |
| TSM900N06CP ROG | TO-252  | 2.5kpcs / 13" Reel |
| TSM900N06CW RPG | SOT-223 | 2.5kpcs / 13" Reel |

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

### Block Diagram



N-Channel MOSFET

### Absolute Maximum Ratings (Tc = 25°C unless otherwise noted)

| Parameter                                          | Symbol    | Limit       |      |         | Unit |
|----------------------------------------------------|-----------|-------------|------|---------|------|
|                                                    |           | IPAK        | DPAK | SOT-223 |      |
| Drain-Source Voltage                               | $V_{DS}$  | 60          |      |         | V    |
| Gate-Source Voltage                                | $V_{GS}$  | ±20         |      |         | V    |
| Continuous Drain Current <sup>(Note 1)</sup>       | $I_D$     | 11          |      |         | A    |
|                                                    |           | 7           |      |         | A    |
| Pulsed Drain Current <sup>(Note 1)</sup>           | $I_{DM}$  | 44          |      |         | A    |
| Single Pulse Avalanche Energy <sup>(Note 3)</sup>  | $E_{AS}$  | 25          |      |         | mJ   |
| Single Pulse Avalanche Current <sup>(Note 3)</sup> | $I_{AS}$  | 7           |      |         | A    |
| Total Power                                        | $P_D$     | 25          | 25   | 4.17    | W    |
| Dissipation                                        |           | 0.2         | 0.2  | 0.014   | W/°C |
| Operating Junction Temperature                     | $T_J$     | 150         |      |         | °C   |
| Storage Temperature Range                          | $T_{STG}$ | -55 to +150 |      |         | °C   |

### Thermal Performance

| Parameter                                | Symbol          | Limit |      |         | Unit |
|------------------------------------------|-----------------|-------|------|---------|------|
|                                          |                 | IPAK  | DPAK | SOT-223 |      |
| Thermal Resistance - Junction to Case    | $R_{\theta JC}$ | 5     | 5    | 30      | °C/W |
| Thermal Resistance - Junction to Ambient | $R_{\theta JA}$ | 62    | 62   | 70      | °C/W |

### Electrical Specifications ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

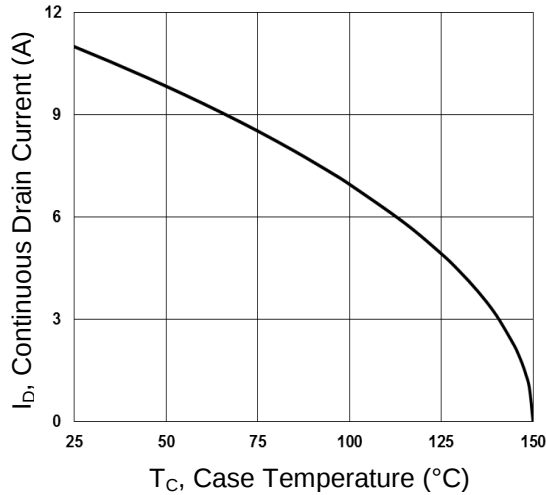
| Parameter                                     | Conditions                                               | Symbol       | Min | Typ  | Max  | Unit |
|-----------------------------------------------|----------------------------------------------------------|--------------|-----|------|------|------|
| Static                                        |                                                          |              |     |      |      |      |
| Drain-Source Breakdown Voltage                | $V_{GS} = 0V, I_D = 250\mu A$                            | $BV_{DSS}$   | 60  | --   | --   | V    |
| Drain-Source On-State Resistance              | $V_{GS} = 10V, I_D = 6A$                                 | $R_{DS(ON)}$ | --  | 76   | 90   | mΩ   |
|                                               | $V_{GS} = 4.5V, I_D = 3A$                                |              | --  | 87   | 100  |      |
| Gate Threshold Voltage                        | $V_{DS} = V_{GS}, I_D = 250\mu A$                        | $V_{GS(TH)}$ | 1.2 | 1.8  | 2.5  | V    |
| Zero Gate Voltage Drain Current               | $V_{DS} = 60V, V_{GS} = 0V$                              | $I_{DSS}$    | --  | --   | 1    | μA   |
|                                               | $V_{DS} = 48V, T_J = 125^{\circ}C$                       |              | --  | --   | 10   |      |
| Gate Body Leakage                             | $V_{GS} = \pm 20V, V_{DS} = 0V$                          | $I_{GSS}$    | --  | --   | ±100 | μA   |
| Forward Transconductance                      | $V_{DS} = 10V, I_D = 3A$                                 | $g_{fs}$     | --  | 4    | --   | S    |
| Dynamic                                       |                                                          |              |     |      |      |      |
| Total Gate Charge <sup>(Note 4,5)</sup>       | $V_{DS} = 48V, I_D = 6A, V_{GS} = 10V$                   | $Q_g$        | --  | 9.3  | --   | nC   |
| Gate-Source Charge <sup>(Note 4,5)</sup>      |                                                          | $Q_{gs}$     | --  | 2.1  | --   |      |
| Gate-Drain Charge <sup>(Note 4,5)</sup>       |                                                          | $Q_{gd}$     | --  | 1.8  | --   |      |
| Input Capacitance                             | $V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$                    | $C_{iss}$    | --  | 500  | --   | pF   |
| Output Capacitance                            |                                                          | $C_{oss}$    | --  | 45   | --   |      |
| Reverse Transfer Capacitance                  |                                                          | $C_{rss}$    | --  | 16   | --   |      |
| Gate Resistance                               | $V_{GS}=0V, V_{DS}=0V, f=1MHz$                           | $R_g$        | --  | 2    | --   | Ω    |
| Switching                                     |                                                          |              |     |      |      |      |
| Turn-On Delay Time <sup>(Note 4,5)</sup>      | $V_{DD} = 30V, V_{GS} = 10V, R_G = 3.3\Omega, I_D = -1A$ | $t_{d(on)}$  | --  | 2.9  | --   | ns   |
| Turn-On Rise Time <sup>(Note 4,5)</sup>       |                                                          | $t_r$        | --  | 9.5  | --   |      |
| Turn-Off Delay Time <sup>(Note 4,5)</sup>     |                                                          | $t_{d(off)}$ | --  | 18.4 | --   |      |
| Turn-Off Fall Time <sup>(Note 4,5)</sup>      |                                                          | $t_f$        | --  | 5.3  | --   |      |
| Source-Drain Diode Ratings and Characteristic |                                                          |              |     |      |      |      |
| Continuous Drain-Source Diode                 | $V_G = V_D = 0V, \text{Force Current}$                   | $I_S$        | --  | --   | 11   | A    |
| Pulse Drain-Source Diode                      |                                                          | $I_{SM}$     | --  | --   | 44   | A    |
| Diode-Source Forward Voltage                  | $V_{GS} = 0V, I_S = 1A$                                  | $V_{SD}$     | --  | --   | 1.2  | V    |
| Reverse Recovery Time <sup>(Note 4)</sup>     | $V_{GS} = 30V, I_S = 1A$                                 | $t_{rr}$     | --  | 23.2 | --   | ns   |
| Reverse Recovery Charge <sup>(Note 4)</sup>   | $dl_F/dt = 100A/\mu s$                                   | $Q_{rr}$     | --  | 14.3 | --   | nC   |

#### Note:

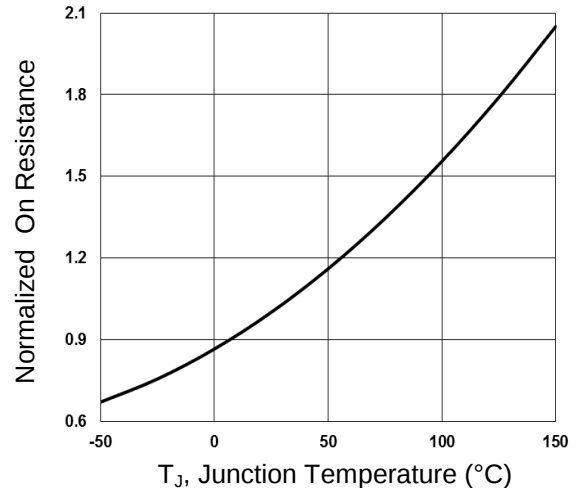
- Limited by maximum junction temperature.
- Repetitive Rating : Pulsed width limited by maximum junction temperature.
- $V_{DD}=25V, V_{GS}=10V, L=1mH, I_{AS}=7A, R_G=25\Omega, \text{Starting } T_J= 25^\circ\text{C}$
- Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- Essentially independent of operating temperature.

### Electrical Characteristics Curve

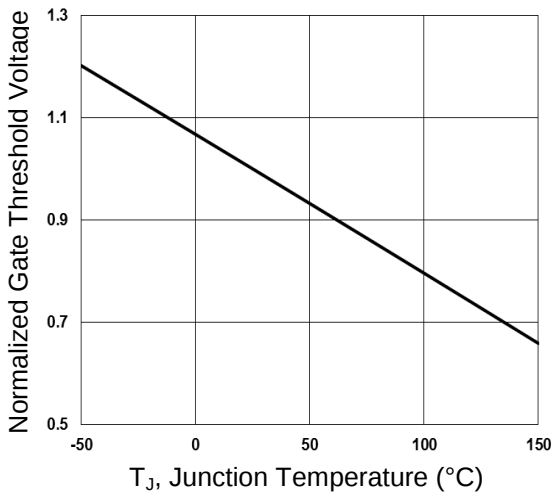
**Continuous Drain Current vs.  $T_c$**



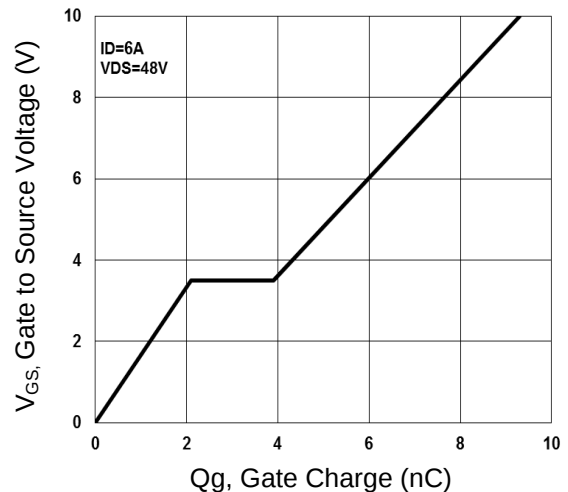
**Normalized  $R_{DS(on)}$  vs.  $T_J$**



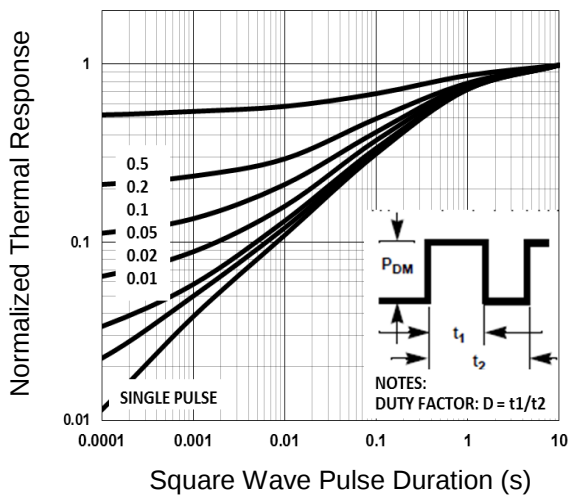
**Normalized  $V_{th}$  vs.  $T_J$**



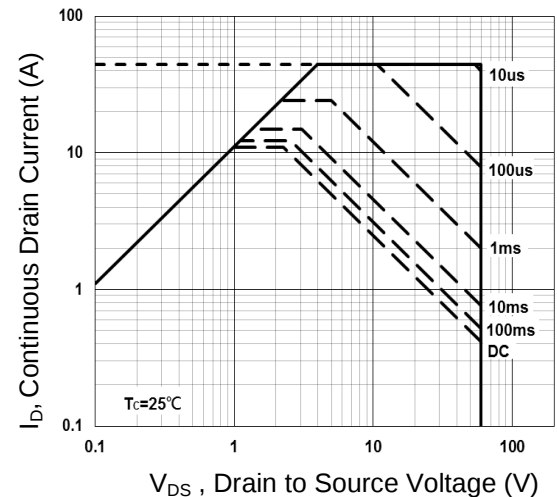
**Gate Charge Waveform**



**Normalized Transient Impedance (TO-251S)**

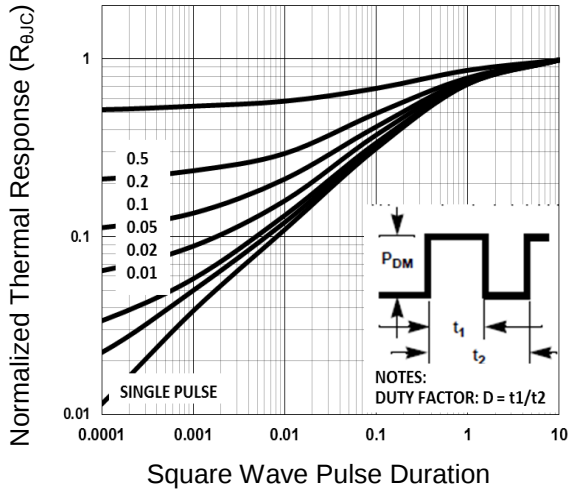


**Maximum Safe Operation Area (TO-251S)**

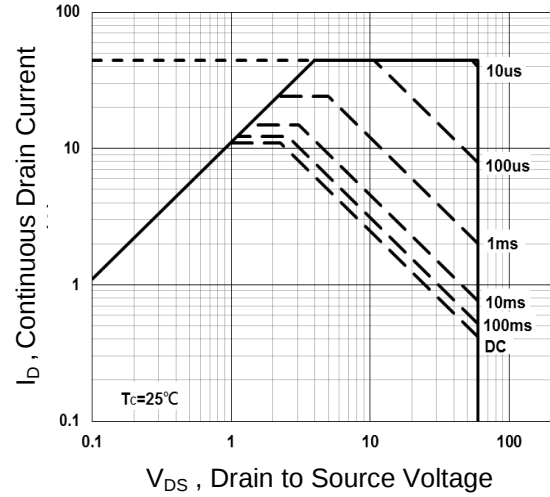


### Electrical Characteristics Curve ( $T_c=25^\circ\text{C}$ , unless otherwise noted)

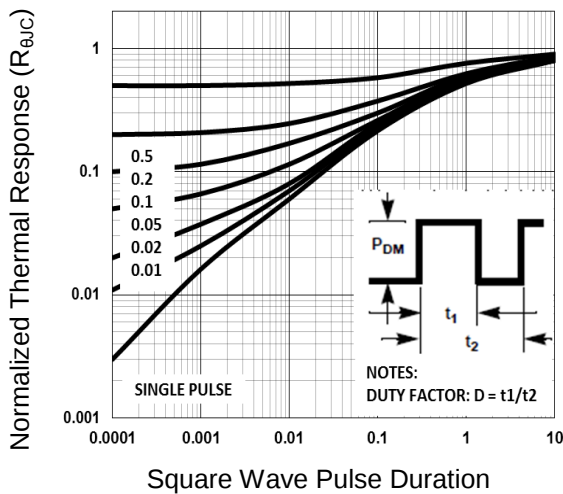
**Normalized Transient Impedance (TO-252)**



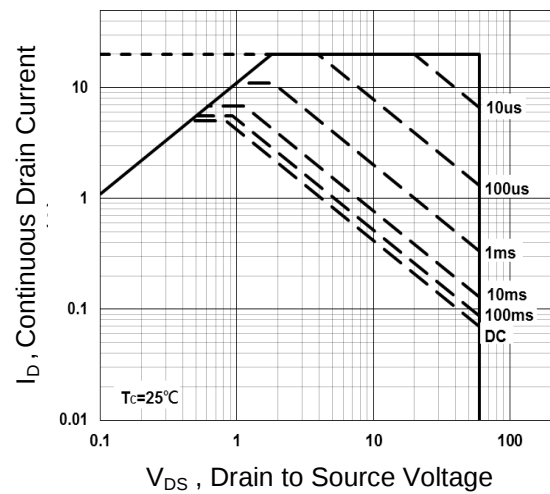
**Maximum Safe Operation Area (TO-252)**



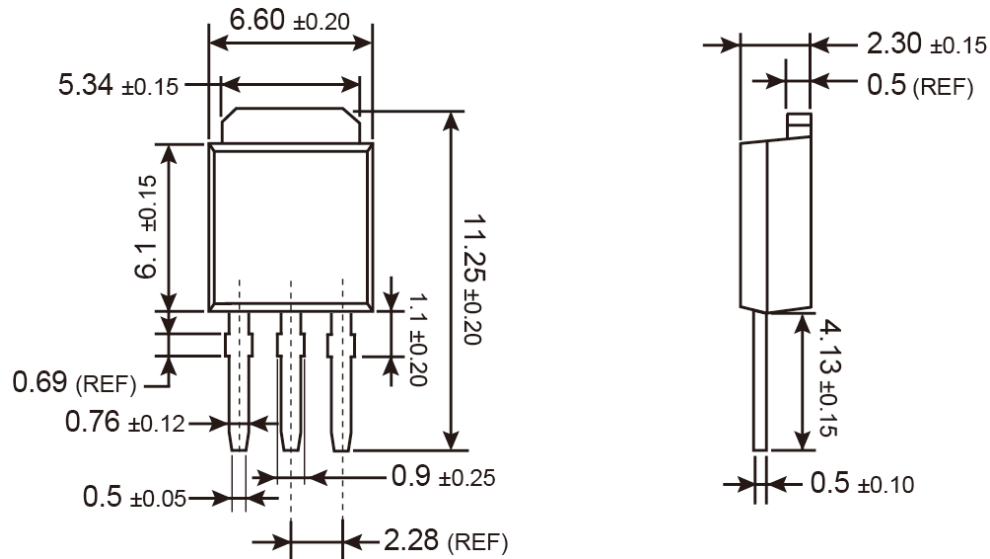
**Normalized Transient Impedance (SOT-223)**



**Maximum Safe Operation Area (SOT-223)**

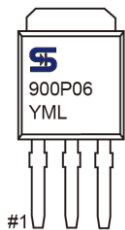


## TO-251S Mechanical Drawing



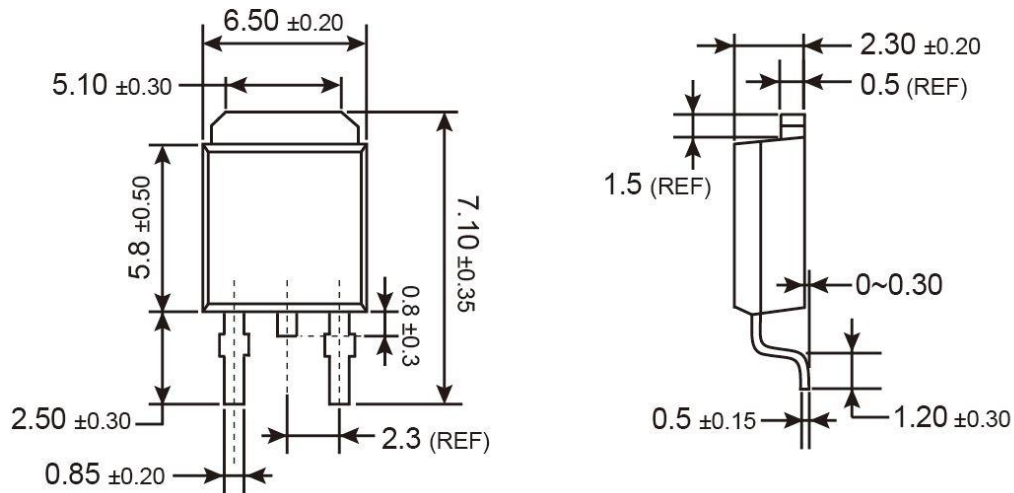
Unit: Millimeters

## Marking Diagram



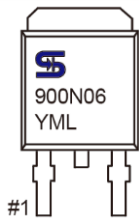
**Y** = Year Code  
**M** = Month Code for Halogen Free Product  
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)  
**L** = Lot Code

### TO-252 Mechanical Drawing



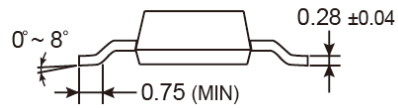
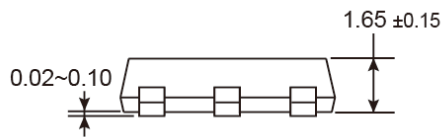
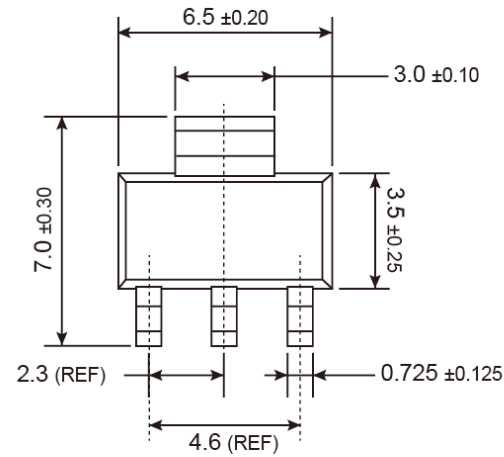
Unit: Millimeters

### Marking Diagram



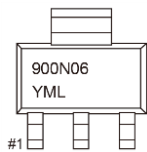
- Y** = Year Code
- M** = Month Code for Halogen Free Product  
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

### SOT-223 Mechanical Drawing



Unit: Millimeters

### Marking Diagram



**Y** = Year Code

**M** = Month Code for Halogen Free Product

(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)

**L** = Lot Code

# TSM900N06

## 60V N-Channel Power MOSFET

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